Renesas Electronics America Inc - R5F21348UDFP#X0 Datasheet

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"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "Embedded - Microcontrollers"

Details	
Product Status	Last Time Buy
Core Processor	R8C
Core Size	16-Bit
Speed	20MHz
Connectivity	I²C, LINbus, SIO, SSU, UART/USART, USB
Peripherals	POR, PWM, Voltage Detect, WDT
Number of I/O	36
Program Memory Size	64KB (64K x 8)
Program Memory Type	FLASH
EEPROM Size	4K x 8
RAM Size	8K x 8
Voltage - Supply (Vcc/Vdd)	1.8V ~ 5.5V
Data Converters	A/D 12x10b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	48-LQFP
Supplier Device Package	48-LQFP (7x7)
Purchase URL	https://www.e-xfl.com/product-detail/renesas-electronics-america/r5f21348udfp-x0

1.1.2 Differences between Groups

Table 1.1 lists the Differences between Groups.

Table 1.1 Differences between Groups

Item	R8C/34U Group	R8C/34K Group
Memory (ROM/RAM)	32 KB/4 KB, 64 KB/8 KB	64 KB/8 KB, 128 KB/10 KB
USB Functions	Peripheral function	Host/peripheral function

1.1.3 Specifications

Tables 1.2 and 1.3 outline the Specifications for R8C/34U Group, R8C/34K Group.

Table 1.2 Specifications for R8C/34U Group, R8C/34K Group (1)

Item	Function	Specification
CPU	Central processing unit	R8C CPU core • Number of fundamental instructions: 89 • Minimum instruction execution time: 50 ns (f(XIN) = 20 MHz, VCC = 2.7 to 5.5 V) 200 ns (f(XIN) = 5 MHz, VCC = 1.8 to 5.5 V) • Multiplier: 16 bits × 16 bits → 32 bits • Multiply-accumulate instruction: 16 bits × 16 bits + 32 bits → 32 bits • Operation mode: Single-chip mode (address space: 1 Mbyte)
Memory	ROM, RAM, Data flash	Refer to **Table 1.4 Product List for R8C/34U Group**, and **Table 1.5 Product List for R8C/34K Group**.
Power Supply Voltage Detection	Voltage detection circuit	• Power-on reset • Voltage detection 3 (detection level of voltage detection 0 and voltage detection 1 selectable)
I/O Ports	Programmable I/O ports	• CMOS I/O ports: 36, selectable pull-up resistor • High current drive ports: 36
Clock	Clock generation circuits	• 4 circuits: XIN clock oscillation circuit, High-speed on-chip oscillator (with frequency adjustment function), Low-speed on-chip oscillator PLL frequency synthesizer • Oscillation stop detection: XIN clock oscillation stop detection function • Frequency divider circuit: Dividing selectable 1, 2, 4, 8, and 16 • Low power consumption modes: Standard operating mode (XIN clock, PLL frequency synthesizer, high-speed on-chip oscillator, low-speed on-chip oscillator), wait mode, stop mode
Interrupts		• Interrupt Vectors: 69 • External: 9 sources ($\overline{\text{INT}}$ × 5, key input × 4) • Priority levels: 7 levels
Watchdog Timer		• 14 bits × 1 (with prescaler) • Reset start selectable • Low-speed on-chip oscillator for watchdog timer selectable
DTC (Data Transfer Controller)		• 1 channel • Activation sources: 30 • Transfer modes: 2 (normal mode, repeat mode)
Timer	Timer RA	8 bits × 1 (with 8-bit prescaler) Timer mode (period timer), pulse output mode (output level inverted every period), event counter mode, pulse width measurement mode, pulse period measurement mode
	Timer RB	8 bits × 1 (with 8-bit prescaler) Timer mode (period timer), programmable waveform generation mode (PWM output), programmable one-shot generation mode, programmable wait one-shot generation mode
	Timer RC	16 bits × 1 (with 4 capture/compare registers) Timer mode (input capture function, output compare function), PWM mode (output 3 pins), PWM2 mode (PWM output pin)
	Timer RF	16 bits × 1 Input capture mode (input × 1) Output compare mode (output × 4)
Serial Interface	UART0, UART1, UART3	Clock synchronous serial I/O/UART × 3 channel
	UART2	Clock synchronous serial I/O, UART, multiprocessor communication function
Synchronous Serial Communication Unit (SSU)		1 (shared with I^2C bus)

Table 1.3 Specifications for R8C/34U Group, R8C/34K Group (2)

Item	Function	Specification
I²C bus		1 (shared with SSU)
LIN Module		Hardware LIN: 1 (timer RA, UART0)
USB Functions	R8C/34U Group	• USB 2.0 specification compliant, Full speed (12 Mbps) supported • USB function controller and USB transceiver incorporated • 5 pipes provided with individual FIFO Arbitrary EP numbers can be specified for PIPE4 to 7 • FIFO size (total 448 bytes: DCP (EP0) = 64 bytes, PIPE4 and PIPE5 = 128 bytes (64-byte double buffer), PIPE6 and PIPE7 = 64 bytes • Supported transfer: DCP = Control transfer IN/OUT, PIPE4 and PIPE5 = Bulk transfer IN/OUT, PIPE6 and PIPE7 = Interrupt transfer IN/OUT
	R8C/34K Group	• USB 2.0 specification compliant, Full speed (12 Mbps) supported • USB Device Controller (UDC), transceiver for USB2.0 are incorporated, and on-chip USB transceiver • 5 pipes provided with individual FIFO Arbitrary EP numbers can be specified for PIPE4 to 7 • USB OTG (On-The-Go) operation is possible • FIFO size (total 448 bytes): DCP (EP0) = 64 bytes, PIPE4 and PIPE5 = 128 bytes (64-byte double buffer), PIPE6 and PIPE7 = 64 bytes • Supported transfer: DCP = Control transfer IN/OUT, PIPE4 and PIPE5 = Bulk transfer IN/OUT, PIPE6 and PIPE7 = Interrupt transfer IN/OUT • When the host controller is selected Automatic scheduling for SOF and packet transmissions Programmable intervals for interrupt transfers
A/D Converter		10-bit resolution × 12 channels, includes sample and hold function, with sweep mode
Comparator B		2 circuits
Flash Memory		• Programming and erasure voltage: VCC = 2.7 to 5.5 V • Programming and erasure endurance: 10,000 times (data flash) 1,000 times (program ROM) • Program security: ROM code protect, ID code check • Debug functions: On-chip debug, on-board flash rewrite function • Background operation (BGO) function (data flash)
Operating Frequency/Supply Voltage		f(XIN) = 20 MHz (VCC = 2.7 to 5.5 V)(USB not used) f(XIN) = 5 MHz (VCC = 1.8 to 5.5 V)(USB not used)
Current consumption		Typ. 7.0 mA (VCC = 5.0 V, f(XIN) = 20 MHz) Typ. 3.5 mA (VCC = 3.0 V, f(XIN) = 10 MHz) Typ. 4.0 μA (VCC = 3.0 V, wait mode) Typ. 2.0 μA (VCC = 3.0 V, stop mode)
Operating Ambient Temperature		−20 to 85°C (N version) −40 to 85°C (D version)
Package		48-pin LQFP Package code: PLQP0048KB-A (previous code: 48P6Q-A)

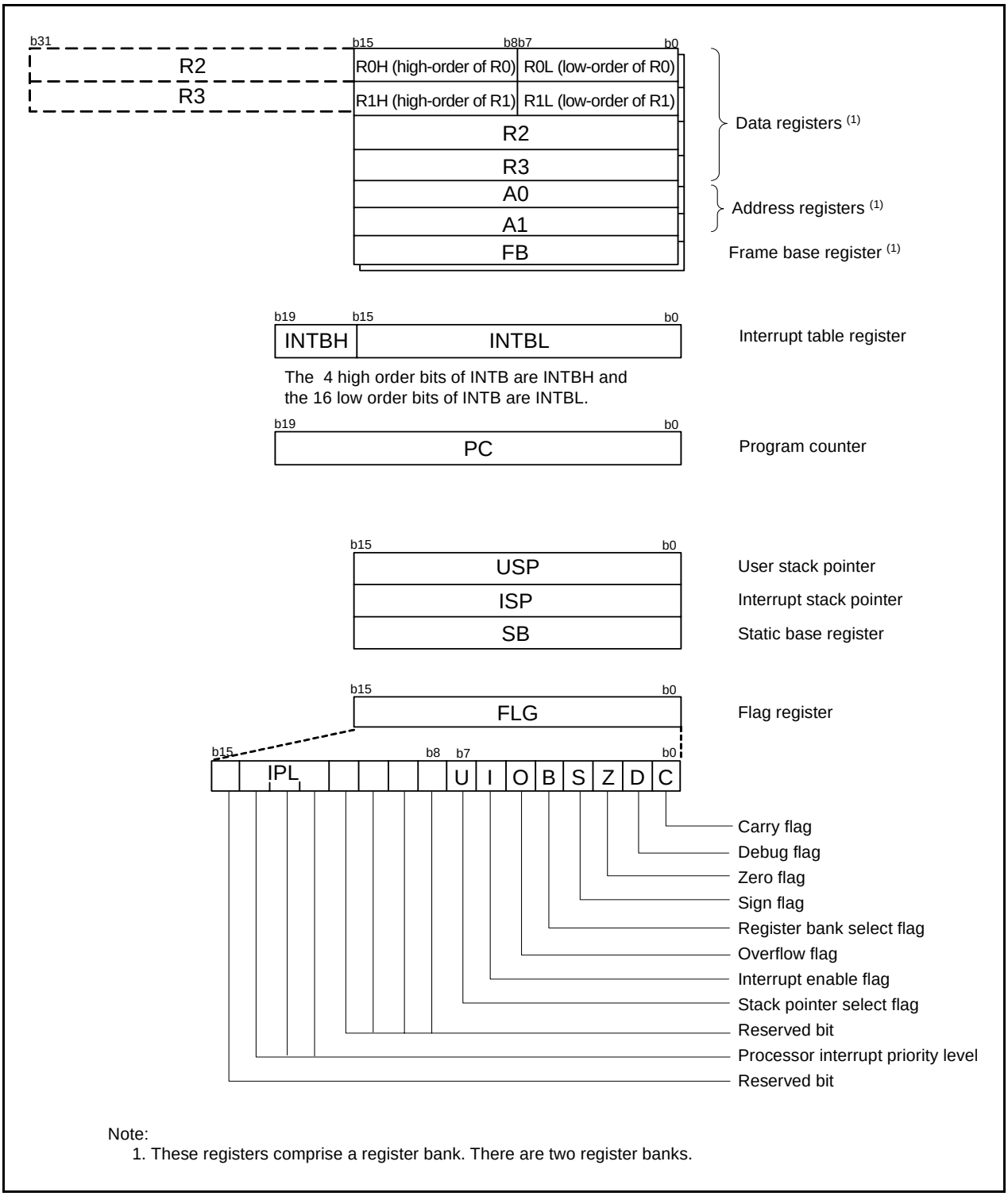
Table 1.7 Pin Name Information by Pin Number (2)

Pin Number	Control Pin	Port	I/O Pin Functions for Peripheral Modules						
			Interrupt	Timer	Serial Interface	SSU	I^2C bus	USB	A/D Converter, Comparator B
41		P0_3		(TRCIOB)	(CLK1)				AN4
42		P0_2		(TRCIOA/ TRCTRG)	(RXD1)				AN5
43		P0_1		(TRCIOA/ TRCTRG)	(TXD1)				AN6
44		P0_0		(TRCIOA/ TRCTRG)					AN7
45		P8_3		(TRFO10/ TRFI)	(RXD3)				
46		P8_2		(TRFO02)	(TXD3)				
47		P8_1		(TRFO01)	(CLK3)				
48		P8_0		(TRFO00)					

Note:
1. Can be assigned to the pin in parentheses by a program.

2. Central Processing Unit (CPU)

Figure 2.1 shows the CPU Registers. The CPU contains 13 registers. R0, R1, R2, R3, A0, A1, and FB configure a register bank. There are two sets of register bank.



Note:
1. These registers comprise a register bank. There are two register banks.

Figure 2.1 CPU Registers

2.1 Data Registers (R0, R1, R2, and R3)

R0 is a 16-bit register for transfer, arithmetic, and logic operations. The same applies to R1 to R3. R0 can be split into high-order bits (R0H) and low-order bits (R0L) to be used separately as 8-bit data registers. R1H and R1L are analogous to R0H and R0L. R2 can be combined with R0 and used as a 32-bit data register (R2R0). R3R1 is analogous to R2R0.

2.2 Address Registers (A0 and A1)

A0 is a 16-bit register for address register indirect addressing and address register relative addressing. It is also used for transfer, arithmetic, and logic operations. A1 is analogous to A0. A1 can be combined with A0 and as a 32-bit address register (A1A0).

2.3 Frame Base Register (FB)

FB is a 16-bit register for FB relative addressing.

2.4 Interrupt Table Register (INTB)

INTB is a 20-bit register that indicates the starting address of an interrupt vector table.

2.5 Program Counter (PC)

PC is 20 bits wide and indicates the address of the next instruction to be executed.

2.6 User Stack Pointer (USP) and Interrupt Stack Pointer (ISP)

The stack pointers (SP), USP and ISP, are each 16 bits wide. The U flag of FLG is used to switch between USP and ISP.

2.7 Static Base Register (SB)

SB is a 16-bit register for SB relative addressing.

2.8 Flag Register (FLG)

FLG is an 11-bit register indicating the CPU state.

2.8.1 Carry Flag (C)

The C flag retains carry, borrow, or shift-out bits that have been generated by the arithmetic and logic unit.

2.8.2 Debug Flag (D)

The D flag is for debugging only. Set it to 0.

2.8.3 Zero Flag (Z)

The Z flag is set to 1 when an arithmetic operation results in 0; otherwise to 0.

2.8.4 Sign Flag (S)

The S flag is set to 1 when an arithmetic operation results in a negative value; otherwise to 0.

2.8.5 Register Bank Select Flag (B)

Register bank 0 is selected when the B flag is 0. Register bank 1 is selected when this flag is set to 1.

2.8.6 Overflow Flag (O)

The O flag is set to 1 when an operation results in an overflow; otherwise to 0.

Table 4.2 SFR Information (2) (1)

Address	Register	Symbol	After Reset
003Ah	Voltage Monitor 2 Circuit Control Register	VW2C	10000010b
003Bh			
003Ch			
003Dh			
003Eh			
003Fh			
0040h			
0041h	Flash Memory Ready Interrupt Control Register	FMRDYIC	XXXXX000b
0042h			
0043h			
0044h			
0045h			
0046h	INT4 Interrupt Control Register	INT4IC	XX00X000b
0047h	Timer RC Interrupt Control Register	TRCIC	XXXXX000b
0048h			
0049h	USB RESUME Interrupt Control Register	USBRSMIC	XXXXX000b
004Ah			
004Bh	UART2 Transmit Interrupt Control Register	S2TIC	XXXXX000b
004Ch	UART2 Receive Interrupt Control Register	S2RIC	XXXXX000b
004Dh	Key Input Interrupt Control Register	KUPIC	XXXXX000b
004Eh	A/D Conversion Interrupt Control Register	ADIC	XXXXX000b
004Fh	SSU Interrupt Control Register/IIC bus Interrupt Control Register (2)	SSUIC/IICIC	XXXXX000b
0050h	Timer RF Compare 1 Interrupt Control Register	CMP1IC	XXXXX000b
0051h	UART0 Transmit Interrupt Control Register	S0TIC	XXXXX000b
0052h	UART0 Receive Interrupt Control Register	S0RIC	XXXXX000b
0053h	UART1 Transmit Interrupt Control Register	S1TIC	XXXXX000b
0054h	UART1 Receive Interrupt Control Register	S1RIC	XXXXX000b
0055h	INT2 Interrupt Control Register	INT2IC	XX00X000b
0056h	Timer RA Interrupt Control Register	TRAIC	XXXXX000b
0057h			
0058h	Timer RB Interrupt Control Register	TRBIC	XXXXX000b
0059h	INT1 Interrupt Control Register	INT1IC	XX00X000b
005Ah	INT3 Interrupt Control Register	INT3IC	XX00X000b
005Bh	Timer RF Interrupt Control Register	TRFIC	XXXXX000b
005Ch	Timer RF Compare 0 Interrupt Control Register	CMP0IC	XXXXX000b
005Dh	INT0 Interrupt Control Register	INT0IC	XX00X000b
005Eh	UART2 Bus Collision Detection Interrupt Control Register	U2BCNIC	XXXXX000b
005Fh	Timer RF Capture Interrupt Control Register	CAPIC	XXXXX000b
0060h			
0061h			
0062h			
0063h			
0064h			
0065h			
0066h			
0067h			
0068h			
0069h			
006Ah			
006Bh	USB INT Interrupt Control Register	USBINTIC	XXXXX000b
006Ch	UART3 Transmit Interrupt Control Register	S3RIC	XXXXX000b
006Dh	UART3 Receive Interrupt Control Register	S3TIC	XXXXX000b
006Eh			
006Fh			
0070h			
0071h			
0072h	Voltage Monitor 1 Interrupt Control Register	VCMP1IC	XXXXX000b
0073h	Voltage Monitor 2 Interrupt Control Register	VCMP2IC	XXXXX000b
0074h			
0075h			
0076h			
0077h			
0078h			
0079h			
007Ah			
007Bh			
007Ch			
007Dh			
007Eh			
007Fh			

X: Undefined

Notes:

1. The blank areas are reserved and cannot be accessed by users.
2. Selectable by the IICSEL bit in the SSUIICSR register.

Table 4.15 SFR Information (15) (1)

Address	Register	Symbol	After Reset
2F00h	USB Module Control Register	USBMC	00X10000b
2F01h	PLL Control Register 0	PLC0	0010X000b
2F02h	PLL Control Register 1	PLC1	00001100b
2F03h	PLL Division Control Register	PLDIV	00001011b
2F04h			
2F05h			
2F06h			
2F07h			
2F08h			
2F09h			
2F0Ah			
2F0Bh			
2F0Ch			
2F0Dh			
2F0Eh			
2F0Fh			
2F10h	USB Pin Select Register 0	USBSR0	00h
2F11h	USB Pin Select Register 1 (2)	USBSR1	00h
2F12h	UART3 Pin Select Register	U3SR	00h
2F13h			
2F14h			
2F15h			
2F16h			
2F17h			
2F18h			
2F19h			
2F1Ah			
2F1Bh			
2F1Ch			
2F1Dh			
2F1Eh			
2F1Fh			
:			
2FFFh			

X: Undefined

Notes:
1. The blank areas are reserved and cannot be accessed by users.
2. This register is not available in the R8C/34U Group.

Table 4.16 ID Code Areas and Option Function Select Area

Address	Area Name	Symbol	After Reset
:			
FFDBh	Option Function Select Register 2	OFS2	(Note 1)
:			
FFDFh	ID1		(Note 2)
:			
FFE3h	ID2		(Note 2)
:			
FFEBh	ID3		(Note 2)
:			
FFEFh	ID4		(Note 2)
:			
FFF3h	ID5		(Note 2)
:			
FFF7h	ID6		(Note 2)
:			
FFFBh	ID7		(Note 2)
:			
FFFFh	Option Function Select Register	OFS	(Note 1)

Notes:
1. The option function select area is allocated in the flash memory, not in the SFRs. Set appropriate values as ROM data by a program.
   Do not write additions to the option function select area. If the block including the option function select area is erased, the option function select area is set to FFh.
   When blank products are shipped, the option function select area is set to FFh. It is set to the written value after written by the user.
   When factory-programming products are shipped, the value of the option function select area is the value programmed by the user.
2. The ID code areas are allocated in the flash memory, not in the SFRs. Set appropriate values as ROM data by a program.
   Do not write additions to the ID code areas. If the block including the ID code areas is erased, the ID code areas are set to FFh.
   When blank products are shipped, the ID code areas are set to FFh. They are set to the written value after written by the user.
   When factory-programming products are shipped, the value of the ID code areas is the value programmed by the user.

Table 5.3 A/D Converter Characteristics

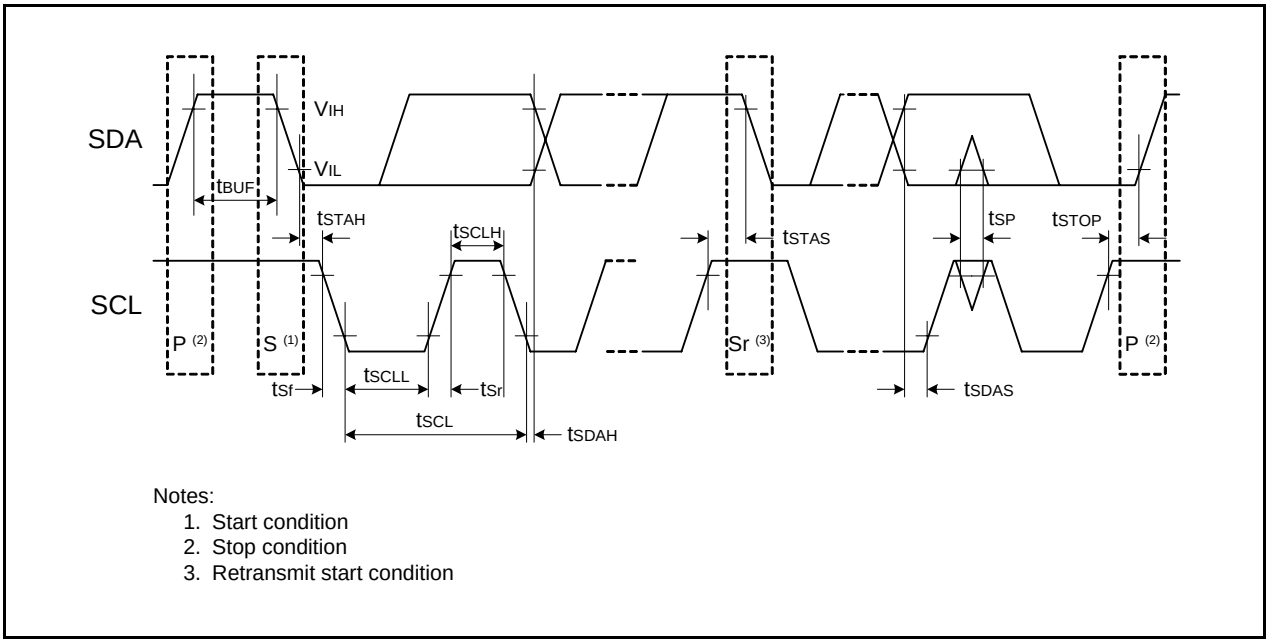
Symbol	Parameter		Conditions		Standard			Unit
					Min.	Typ.	Max.	
—	Resolution		V_{ref} = AV_{CC}		—	—	10	Bit
—	Absolute accuracy	10-bit mode	V_{ref} = AV_{CC} = 5.0 V	AN0 to AN7 input, AN8 to AN11 input	—	—	±3	LSB
			V_{ref} = AV_{CC} = 3.3 V	AN0 to AN7 input, AN8 to AN11 input	—	—	±5	LSB
			V_{ref} = AV_{CC} = 3.0 V	AN0 to AN7 input, AN8 to AN11 input	—	—	±5	LSB
			V_{ref} = AV_{CC} = 2.2 V	AN0 to AN7 input, AN8 to AN11 input	—	—	±5	LSB
		8-bit mode	V_{ref} = AV_{CC} = 5.0 V	AN0 to AN7 input, AN8 to AN11 input	—	—	±2	LSB
			V_{ref} = AV_{CC} = 3.3 V	AN0 to AN7 input, AN8 to AN11 input	—	—	±2	LSB
			V_{ref} = AV_{CC} = 3.0 V	AN0 to AN7 input, AN8 to AN11 input	—	—	±2	LSB
			V_{ref} = AV_{CC} = 2.2 V	AN0 to AN7 input, AN8 to AN11 input	—	—	±2	LSB
ϕAD	A/D conversion clock		4.0 V ≤ V_{ref} = AV_{CC} ≤ 5.5 V (2)		2	—	20	MHz
			3.2 V ≤ V_{ref} = AV_{CC} ≤ 5.5 V (2)		2	—	16	MHz
			2.7 V ≤ V_{ref} = AV_{CC} ≤ 5.5 V (2)		2	—	10	MHz
			2.2 V ≤ V_{ref} = AV_{CC} ≤ 5.5 V (2)		2	—	5	MHz
—	Tolerance level impedance				—	3	—	kΩ
t_{CONV}	Conversion time	10-bit mode	V_{ref} = AV_{CC} = 5.0 V, ϕAD = 20 MHz		2.2	—	—	µs
		8-bit mode	V_{ref} = AV_{CC} = 5.0 V, ϕAD = 20 MHz		2.2	—	—	µs
t_{SAMP}	Sampling time		ϕAD = 20 MHz		0.8	—	—	µs
I_{Vref}	V_{ref} current		V_{CC} = 5.0 V, XIN = f1 = ϕAD = 20 MHz		—	45	—	µA
V_{ref}	Reference voltage				2.2	—	AV_{CC}	V
VIA	Analog input voltage(3)				0	—	Vref	V
OCVREF	On-chip reference voltage		2 MHz ≤ ϕAD ≤ 4 MHz		1.19	1.34	1.49	V

Notes:
1. V_{CC}/AV_{CC} = V_{ref} = 2.2 to 5.5 V, V_{SS} = 0 V, and T_{opr} = –20 to 85 °C (N version)/-40 to 85 °C (D version), unless otherwise specified.
2. The A/D conversion result will be undefined in wait mode, stop mode, when the flash memory stops, and in low-current-consumption mode. Do not perform A/D conversion in these states or transition to these states during A/D conversion.
3. When the analog input voltage is over the reference voltage, the A/D conversion result will be 3FFh in 10-bit mode and FFh in 8-bit mode.

Table 5.16 Timing Requirements of I²C bus Interface

Symbol	Parameter	Condition	Standard			Unit
			Min.	Typ.	Max.	
t_{SCL}	SCL input cycle time		$12t_{CYC} + 600$ (2)	—	—	ns
t_{SCLH}	SCL input “H” width		$3t_{CYC} + 300$ (2)	—	—	ns
t_{SCLL}	SCL input “L” width		$5t_{CYC} + 500$ (2)	—	—	ns
t_{sf}	SCL, SDA input fall time		—	—	300	ns
t_{SP}	SCL, SDA input spike pulse rejection time		—	—	$1t_{CYC}$ (2)	ns
t_{BUF}	SDA input bus-free time		$5t_{CYC}$ (2)	—	—	ns
t_{STAH}	Start condition input hold time		$3t_{CYC}$ (2)	—	—	ns
t_{STAS}	Retransmit start condition input setup time		$3t_{CYC}$ (2)	—	—	ns
t_{STOP}	Stop condition input setup time		$3t_{CYC}$ (2)	—	—	ns
t_{SDAS}	Data input setup time		$1t_{CYC} + 40$ (2)	—	—	ns
t_{SDAH}	Data input hold time		10	—	—	ns

Notes:
1. V_{CC} = 1.8 to 5.5 V, V_{SS} = 0 V, and T_{opr} = –20 to 85 °C (N version)/-40 to 85 °C (D version), unless otherwise specified.
2. $1t_{CYC} = 1/f1(s)$



Notes:
1. Start condition
2. Stop condition
3. Retransmit start condition

Figure 5.9 I/O Timing of I²C bus Interface

Table 5.36 Serial Interface

Symbol	Parameter	Standard		Unit
		Min.	Max.	
$t_{c(CK)}$	CLKi input cycle time	800	—	ns
$t_{W(CKH)}$	CLKi input “H” width	400	—	ns
$t_{W(CKL)}$	CLKi input “L” width	400	—	ns
$t_{d(C-Q)}$	TXDi output delay time	—	200	ns
$t_{h(C-Q)}$	TXDi hold time	0	—	ns
$t_{su(D-C)}$	RXDi input setup time	150	—	ns
$t_{h(C-D)}$	RXDi input hold time	90	—	ns

i = 0 to 3

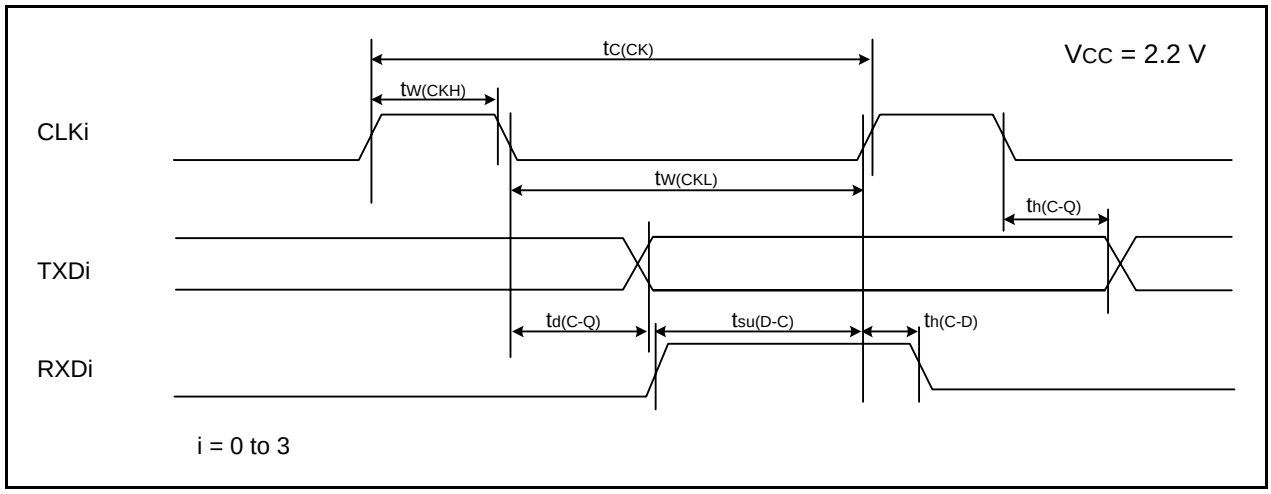


Figure 5.23 Serial Interface Timing Diagram when Vcc = 2.2 V

Table 5.37 External Interrupt $\overline{INTi}$ (i = 0 to 4) Input, Key Input Interrupt $\overline{KIi}$ (i = 0 to 3)

Symbol	Parameter	Standard		Unit
		Min.	Max.	
$t_{W(INH)}$	$\overline{INTi}$ input “H” width, $\overline{KIi}$ input “H” width	1000 (1)	—	ns
$t_{W(INL)}$	$\overline{INTi}$ input “L” width, $\overline{KIi}$ input “L” width	1000 (2)	—	ns

Notes:
1. When selecting the digital filter by the $\overline{INTi}$ input filter select bit, use an $\overline{INTi}$ input HIGH width of either (1/digital filter clock frequency × 3) or the minimum value of standard, whichever is greater.
2. When selecting the digital filter by the $\overline{INTi}$ input filter select bit, use an $\overline{INTi}$ input LOW width of either (1/digital filter clock frequency × 3) or the minimum value of standard, whichever is greater.

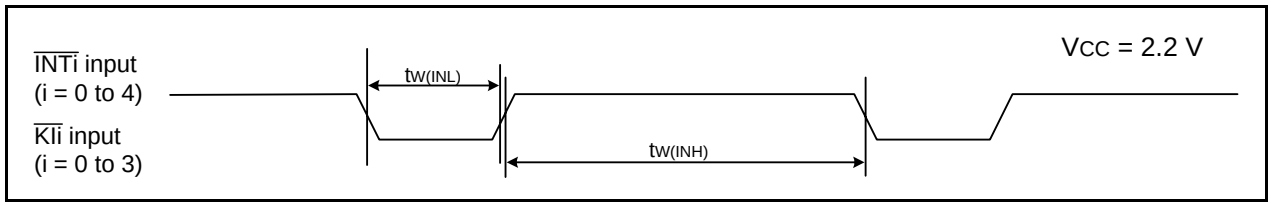


Figure 5.24 Input Timing Diagram for External Interrupt $\overline{INTi}$ and Key Input Interrupt $\overline{KIi}$ when Vcc = 2.2 V

Table 5.39 Recommended Operating Conditions (1)

Symbol	Parameter				Conditions	Standard			Unit
						Min.	Typ.	Max.	
V_{CC}/AV_{CC}	Supply voltage	When USB function is used				3.0	5.0	5.5	V
		When USB function is not used				1.8	5.0	5.5	V
UV_{CC}	USB Supply Voltage (When UVCC pin is input)	When USB function is used			V_{CC}/AV_{CC} = 3.0 to 3.6 V	—	V_{CC}/AV_{CC} (4)	—	V
		When USB function is not used			V_{CC}/AV_{CC} = 1.8 to 5.5 V	—	V_{CC}/AV_{CC} (4)	—	V
V_{SS}/AV_{SS}	Supply voltage					—	0	—	V
V_{IH}	Input “H” voltage	Other than CMOS input				0.8 V_{CC}	—	V_{CC}	V
		CMOS input	Input level switching function (I/O port)	Input level selection: 0.35 V_{CC}	4.0 V ≤ V_{CC} ≤ 5.5 V	0.5 V_{CC}	—	V_{CC}	V
					2.7 V ≤ V_{CC} < 4.0 V	0.55 V_{CC}	—	V_{CC}	V
					1.8 V ≤ V_{CC} < 2.7 V	0.65 V_{CC}	—	V_{CC}	V
				Input level selection: 0.5 V_{CC}	4.0 V ≤ V_{CC} ≤ 5.5 V	0.65 V_{CC}	—	V_{CC}	V
					2.7 V ≤ V_{CC} < 4.0 V	0.7 V_{CC}	—	V_{CC}	V
					1.8 V ≤ V_{CC} < 2.7 V	0.8 V_{CC}	—	V_{CC}	V
				Input level selection: 0.7 V_{CC}	4.0 V ≤ V_{CC} ≤ 5.5 V	0.85 V_{CC}	—	V_{CC}	V
					2.7 V ≤ V_{CC} < 4.0 V	0.85 V_{CC}	—	V_{CC}	V
					1.8 V ≤ V_{CC} < 2.7 V	0.85 V_{CC}	—	V_{CC}	V
		External clock input (XOUT)				1.2	—	V_{CC}	V
V_{IL}	Input “L” voltage	Other than CMOS input				0	—	0.2 V_{CC}	V
		CMOS input	Input level switching function (I/O port)	Input level selection: 0.35 V_{CC}	4.0 V ≤ V_{CC} ≤ 5.5 V	0	—	0.2 V_{CC}	V
					2.7 V ≤ V_{CC} < 4.0 V	0	—	0.2 V_{CC}	V
					1.8 V ≤ V_{CC} < 2.7 V	0	—	0.2 V_{CC}	V
				Input level selection: 0.5 V_{CC}	4.0 V ≤ V_{CC} ≤ 5.5 V	0	—	0.4 V_{CC}	V
					2.7 V ≤ V_{CC} < 4.0 V	0	—	0.3 V_{CC}	V
					1.8 V ≤ V_{CC} < 2.7 V	0	—	0.2 V_{CC}	V
				Input level selection: 0.7 V_{CC}	4.0 V ≤ V_{CC} ≤ 5.5 V	0	—	0.55 V_{CC}	V
					2.7 V ≤ V_{CC} < 4.0 V	0	—	0.45 V_{CC}	V
					1.8 V ≤ V_{CC} < 2.7 V	0	—	0.35 V_{CC}	V
		External clock input (XOUT)				0	—	0.4	V
$I_{OH(sum)}$	Peak sum output “H” current	Sum of all pins $I_{OH(peak)}$				—	—	–160	mA
$I_{OH(sum)}$	Average sum output “H” current	Sum of all pins $I_{OH(avg)}$				—	—	–80	mA
$I_{OH(peak)}$	Peak output “H” current	Drive capacity Low				—	—	–10	mA
		Drive capacity High				—	—	–40	mA
$I_{OH(avg)}$	Average output “H” current	Drive capacity Low				—	—	–5	mA
		Drive capacity High				—	—	–20	mA
$I_{OL(sum)}$	Peak sum output “L” current	Sum of all pins $I_{OL(peak)}$				—	—	160	mA
$I_{OL(sum)}$	Average sum output “L” current	Sum of all pins $I_{OL(avg)}$				—	—	80	mA
$I_{OL(peak)}$	Peak output “L” current	Drive capacity Low				—	—	10	mA
		Drive capacity High				—	—	40	mA
$I_{OL(avg)}$	Average output “L” current	Drive capacity Low				—	—	5	mA
		Drive capacity High				—	—	20	mA
$f_{(XIN)}$	XIN clock input oscillation frequency				2.7 V ≤ V_{CC} ≤ 5.5 V	—	—	20	MHz
					1.8 V ≤ V_{CC} < 2.7 V	—	—	5	MHz
fOCO40M	When used as the count source for timer RC (3)				2.7 V ≤ V_{CC} ≤ 5.5 V	32	—	40	MHz
fOCO-F	fOCO-F frequency				2.7 V ≤ V_{CC} ≤ 5.5 V	—	—	20	MHz
					1.8 V ≤ V_{CC} < 2.7 V	—	—	5	MHz
—	System clock frequency				2.7 V ≤ V_{CC} ≤ 5.5 V	—	—	20	MHz
					1.8 V ≤ V_{CC} < 2.7 V	—	—	5	MHz
$f_{(BCLK)}$	CPU clock frequency				2.7 V ≤ V_{CC} ≤ 5.5 V	—	—	20	MHz
					1.8 V ≤ V_{CC} < 2.7 V	—	—	5	MHz
$t_{su(PLL)}$	PLL frequency symthesizer stabilization wait time				4.0 V ≤ V_{CC} ≤ 5.5 V	—	—	2	ms
					2.7 V ≤ V_{CC} < 4.0 V	—	—	3	ms

Notes:
1. V_{CC} = 1.8 to 5.5 V and T_{opr} = –20 to 85 °C (N version)/-40 to 85 °C (D version), unless otherwise specified.
2. The average output current indicates the average value of current measured during 100 ms.
3. fOCO40M can be used as the count source for timer RC in the range of V_{CC} = 2.7 to 5.5 V.
4. Connect V_{CC}/AV_{CC} for the UV_{CC} pin input.

Table 5.43 Flash Memory (Program ROM) Electrical Characteristics

Symbol	Parameter	Conditions	Standard			Unit
			Min.	Typ.	Max.	
—	Program/erase endurance (2)		1,000 (3)	—	—	times
—	Byte program time		—	80	500	µs
—	Block erase time		—	0.3	—	s
$t_{d(SR-SUS)}$	Time delay from suspend request until suspend		—	—	5 + CPU clock × 3 cycles	ms
—	Interval from erase start/restart until following suspend request		0	—	—	µs
—	Time from suspend until erase restart		—	—	30 + CPU clock × 1 cycle	µs
$t_{d(CMDRST-READY)}$	Time from when command is forcibly stopped until reading is enabled		–	–	30 + CPU clock × 1 cycle	µs
—	Program, erase voltage		2.7	—	5.5	V
—	Read voltage		1.8	—	5.5	V
—	Program, erase temperature		0	—	60	°C
—	Data hold time (7)	Ambient temperature = 55 °C	20	—	—	year

Notes:
1. V_{CC} = 2.7 to 5.5 V and T_{opr} = 0 to 60 °C, unless otherwise specified.
2. Definition of programming/erasure endurance
   The programming and erasure endurance is defined on a per-block basis.
   If the programming and erasure endurance is n (n = 1,000), each block can be erased n times. For example, if 1,024 1-byte writes are performed to different addresses in block A, a 1 Kbyte block, and then the block is erased, the programming/erasure endurance still stands at one. However, the same address must not be programmed more than once per erase operation (overwriting prohibited).
3. Endurance to guarantee all electrical characteristics after program and erase. (1 to Min. value can be guaranteed.)
4. In a system that executes multiple programming operations, the actual erasure count can be reduced by writing to sequential addresses in turn so that as much of the block as possible is used up before performing an erase operation. For example, when programming groups of 16 bytes, the effective number of rewrites can be minimized by programming up to 128 groups before erasing them all in one operation. It is also advisable to retain data on the erasure endurance of each block and limit the number of erase operations to a certain number.
5. If an error occurs during block erase, attempt to execute the clear status register command, then execute the block erase command at least three times until the erase error does not occur.
6. Customers desiring program/erase failure rate information should contact their Renesas technical support representative.
7. The data hold time includes time that the power supply is off or the clock is not supplied.

Table 5.44 Flash Memory (Data flash Block A to Block D) Electrical Characteristics

Symbol	Parameter	Conditions	Standard			Unit
			Min.	Typ.	Max.	
—	Program/erase endurance (2)		10,000 (3)	—	—	times
—	Byte program time (program/erase endurance ≤ 1,000 times)		—	160	1500	µs
—	Byte program time (program/erase endurance > 1,000 times)		—	300	1500	µs
—	Block erase time (program/erase endurance ≤ 1,000 times)		—	0.2	1	s
—	Block erase time (program/erase endurance > 1,000 times)		—	0.3	1	s
$t_{d(SR-SUS)}$	Time delay from suspend request until suspend		—	—	5 + CPU clock × 3 cycles	ms
—	Interval from erase start/restart until following suspend request		0	—	—	µs
—	Time from suspend until erase restart		—	—	30 + CPU clock × 1 cycle	µs
$t_{d(CMDRST-READY)}$	Time from when command is forcibly stopped until reading is enabled		–	–	30 + CPU clock × 1 cycle	µs
—	Program, erase voltage		2.7	—	5.5	V
—	Read voltage		1.8	—	5.5	V
—	Program, erase temperature		–20 (7)	—	85	°C
—	Data hold time (8)	Ambient temperature = 55 °C	20	—	—	year

Notes:
1. V_{CC} = 2.7 to 5.5 V and T_{opr} = –20 to 85 °C (N version)/-40 to 85 °C (D version), unless otherwise specified.
2. Definition of programming/erasure endurance
   The programming and erasure endurance is defined on a per-block basis.
   If the programming and erasure endurance is n (n = 10,000), each block can be erased n times. For example, if 1,024 1-byte writes are performed to different addresses in block A, a 1 Kbyte block, and then the block is erased, the programming/erasure endurance still stands at one. However, the same address must not be programmed more than once per erase operation (overwriting prohibited).
3. Endurance to guarantee all electrical characteristics after program and erase. (1 to Min. value can be guaranteed.)
4. In a system that executes multiple programming operations, the actual erasure count can be reduced by writing to sequential addresses in turn so that as much of the block as possible is used up before performing an erase operation. For example, when programming groups of 16 bytes, the effective number of rewrites can be minimized by programming up to 128 groups before erasing them all in one operation. In addition, averaging the erasure endurance between blocks A to D can further reduce the actual erasure endurance. It is also advisable to retain data on the erasure endurance of each block and limit the number of erase operations to a certain number.
5. If an error occurs during block erase, attempt to execute the clear status register command, then execute the block erase command at least three times until the erase error does not occur.
6. Customers desiring program/erase failure rate information should contact their Renesas technical support representative.
7. –40 °C for D version.
8. The data hold time includes time that the power supply is off or the clock is not supplied.

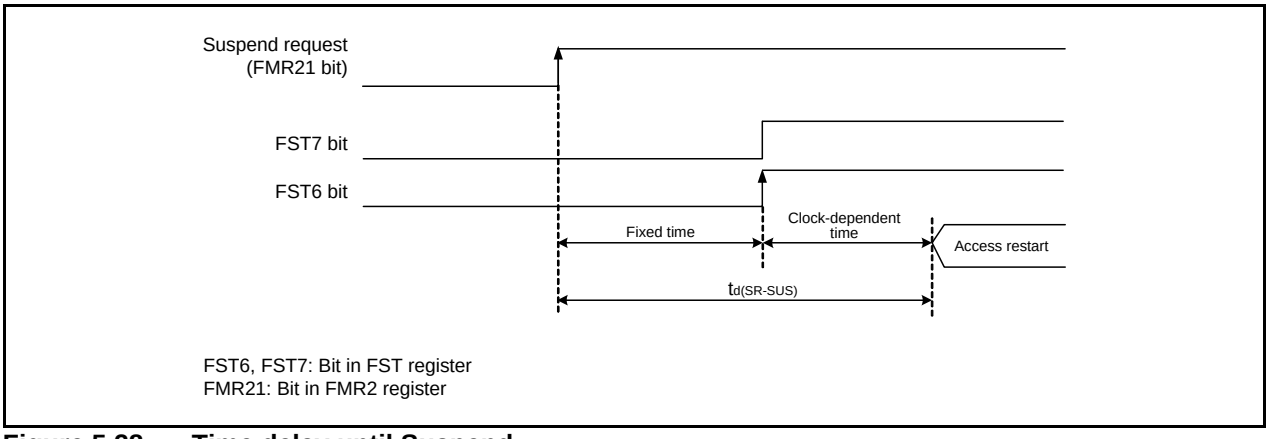


Figure 5.28 Time delay until Suspend

Table 5.45 Voltage Detection 0 Circuit Electrical Characteristics

Symbol	Parameter	Condition	Standard			Unit
			Min.	Typ.	Max.	
V_{det0}	Voltage detection level Vdet0_0 (2)		1.80	1.90	2.05	V
	Voltage detection level Vdet0_1 (2)		2.15	2.35	2.50	V
	Voltage detection level Vdet0_2 (2)		2.70	2.85	3.05	V
	Voltage detection level Vdet0_3 (2)		3.55	3.80	4.05	V
—	Voltage detection 0 circuit response time (4)	At the falling of V_{CC} from 5.0 V to (Vdet0_0 – 0.1) V	—	6	150	µs
—	Voltage detection circuit self power consumption	VCA25 = 1, V_{CC} = 5.0 V	—	1.5	—	µA
$t_{d(E-A)}$	Waiting time until voltage detection circuit operation starts (3)		—	—	100	µs

Notes:
1. The measurement condition is V_{CC} = 1.8 to 5.5 V and T_{opr} = –20 to 85 °C (N version)/-40 to 85 °C (D version).
2. Select the voltage detection level with bits VDSEL0 and VDSEL1 in the OFS register.
3. Necessary time until the voltage detection circuit operates when setting to 1 again after setting the VCA25 bit in the VCA2 register to 0.
4. Time until the voltage monitor 0 reset is generated after the voltage passes V_{det0}.

Table 5.46 Voltage Detection 1 Circuit Electrical Characteristics

Symbol	Parameter	Condition	Standard			Unit
			Min.	Typ.	Max.	
V_{det1}	Voltage detection level Vdet1_0 (2)	At the falling of V_{CC}	2.00	2.20	2.40	V
	Voltage detection level Vdet1_1 (2)	At the falling of V_{CC}	2.15	2.35	2.55	V
	Voltage detection level Vdet1_2 (2)	At the falling of V_{CC}	2.30	2.50	2.70	V
	Voltage detection level Vdet1_3 (2)	At the falling of V_{CC}	2.45	2.65	2.85	V
	Voltage detection level Vdet1_4 (2)	At the falling of V_{CC}	2.60	2.80	3.00	V
	Voltage detection level Vdet1_5 (2)	At the falling of V_{CC}	2.75	2.95	3.15	V
	Voltage detection level Vdet1_6 (2)	At the falling of V_{CC}	2.85	3.10	3.40	V
	Voltage detection level Vdet1_7 (2)	At the falling of V_{CC}	3.00	3.25	3.55	V
	Voltage detection level Vdet1_8 (2)	At the falling of V_{CC}	3.15	3.40	3.70	V
	Voltage detection level Vdet1_9 (2)	At the falling of V_{CC}	3.30	3.55	3.85	V
	Voltage detection level Vdet1_A (2)	At the falling of V_{CC}	3.45	3.70	4.00	V
	Voltage detection level Vdet1_B (2)	At the falling of V_{CC}	3.60	3.85	4.15	V
	Voltage detection level Vdet1_C (2)	At the falling of V_{CC}	3.75	4.00	4.30	V
	Voltage detection level Vdet1_D (2)	At the falling of V_{CC}	3.90	4.15	4.45	V
	Voltage detection level Vdet1_E (2)	At the falling of V_{CC}	4.05	4.30	4.60	V
	Voltage detection level Vdet1_F (2)	At the falling of V_{CC}	4.20	4.45	4.75	V
—	Hysteresis width at the rising of V_{CC} in voltage detection 1 circuit	Vdet1_0 to Vdet1_5 selected	—	0.07	—	V
		Vdet1_6 to Vdet1_F selected	—	0.10	—	V
—	Voltage detection 1 circuit response time (3)	At the falling of V_{CC} from 5.0 V to (Vdet1_0 – 0.1) V	—	60	150	µs
—	Voltage detection circuit self power consumption	VCA26 = 1, V_{CC} = 5.0 V	—	1.7	—	µA
$t_{d(E-A)}$	Waiting time until voltage detection circuit operation starts (4)		—	—	100	µs

Notes:
1. The measurement condition is V_{CC} = 1.8 to 5.5 V and T_{opr} = –20 to 85 °C (N version)/-40 to 85 °C (D version).
2. Select the voltage detection level with bits VD1S0 to VD1S3 in the VD1LS register.
3. Time until the voltage monitor 1 interrupt request is generated after the voltage passes V_{det1}.
4. Necessary time until the voltage detection circuit operates when setting to 1 again after setting the VCA26 bit in the VCA2 register to 0.

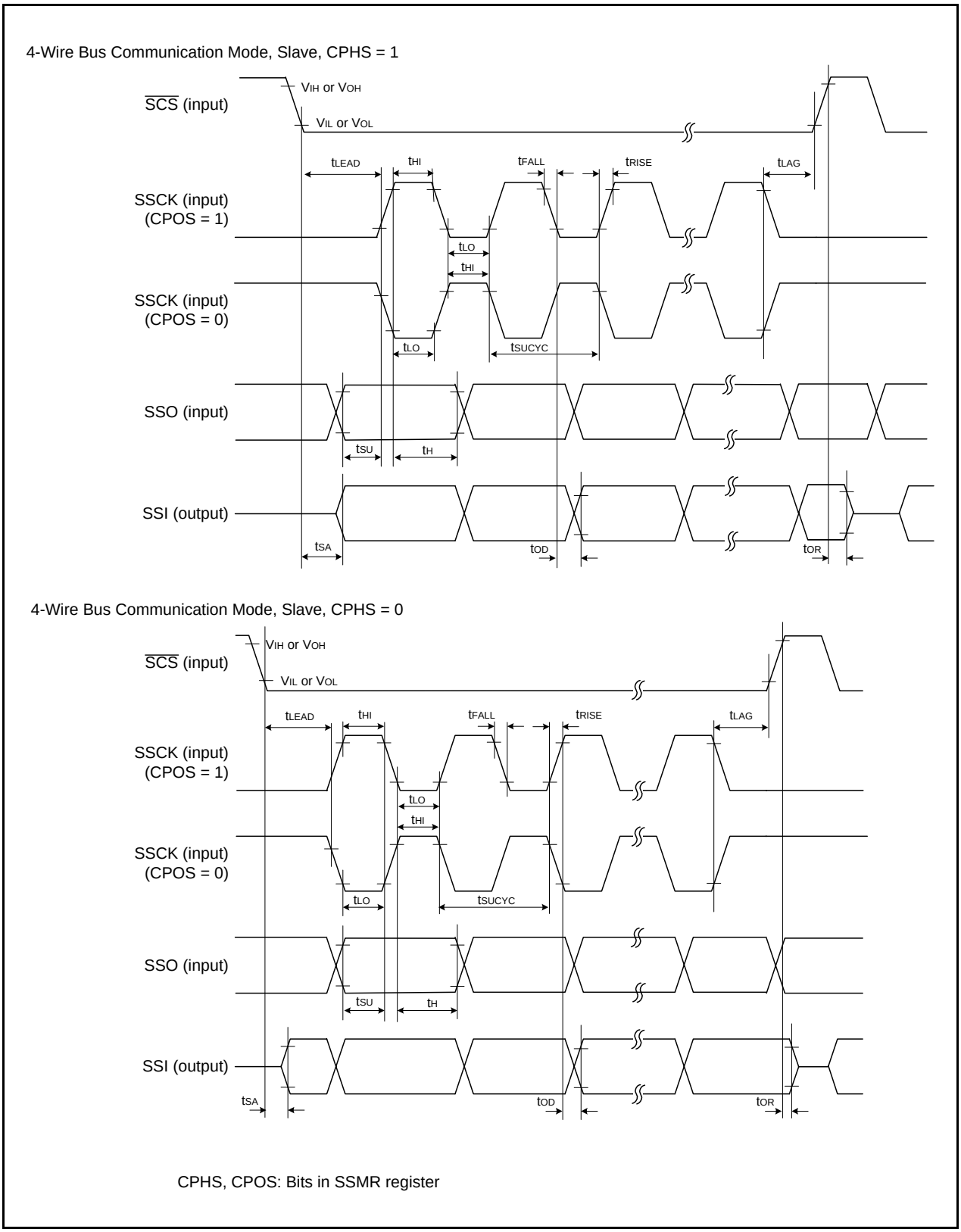


Figure 5.31 I/O Timing of Synchronous Serial Communication Unit (SSU) (Slave)

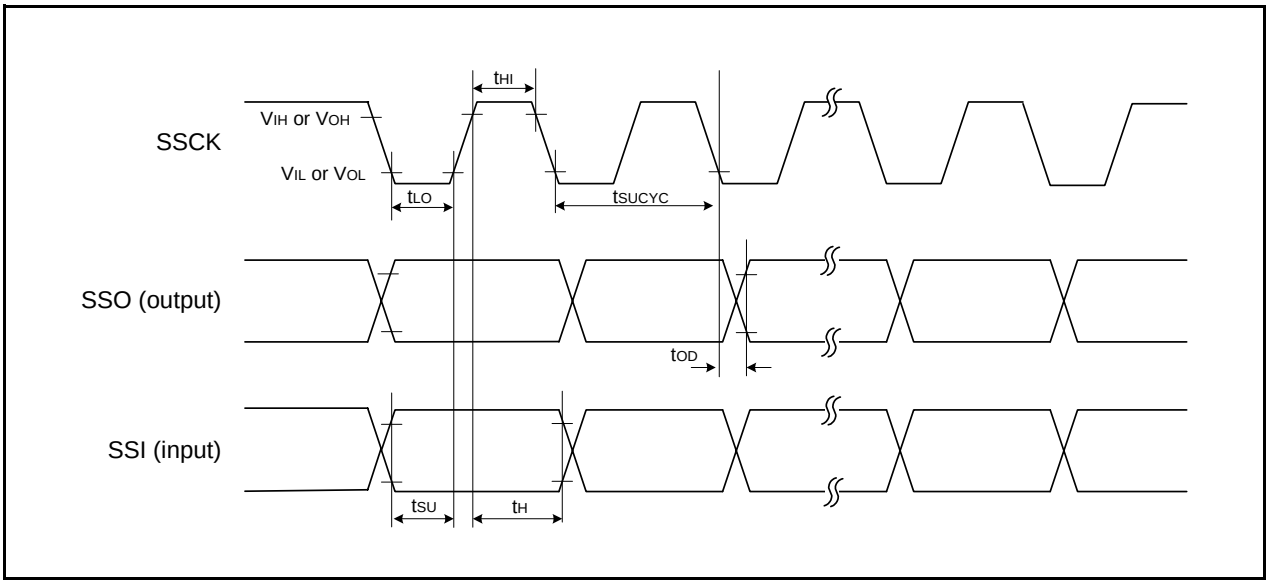


Figure 5.32 I/O Timing of Synchronous Serial Communication Unit (SSU) (Clock Synchronous Communication Mode)

Table 5.54 Electrical Characteristics (1) [4.2 V ≤ Vcc ≤ 5.5 V]

Symbol	Parameter		Condition		Standard			Unit
					Min.	Typ.	Max.	
V_{OH}	Output "H" voltage	Other than XOUT	Drive capacity High V_{CC} = 5 V	I_{OH} = –20 mA	V_{CC} – 2.0	—	V_{CC}	V
			Drive capacity Low V_{CC} = 5 V	I_{OH} = –5 mA	V_{CC} – 2.0	—	V_{CC}	V
		XOUT	V_{CC} = 5 V	I_{OH} = –200 µA	1.0	—	V_{CC}	V
V_{OL}	Output "L" voltage	Other than XOUT	Drive capacity High V_{CC} = 5 V	I_{OL} = 20 mA	—	—	2.0	V
			Drive capacity Low V_{CC} = 5 V	I_{OL} = 5 mA	—	—	2.0	V
		XOUT	V_{CC} = 5 V	I_{OL} = 200 µA	—	—	0.5	V
V_{T+}-V_{T-}	Hysteresis	$\overline{INT0}$, $\overline{INT1}$, $\overline{INT2}$, $\overline{INT3}$, $\overline{INT4}$, $\overline{KI0}$, $\overline{KI1}$, $\overline{KI2}$, $\overline{KI3}$, TRAIO,TRCIOA, TRCIOB, TRCIOC, TRCIOD, TRFI, USB_OVRCURA, USB_VBUS, USB_ID, USB_OVRCURB, $\overline{TRCTRG}$, TRCCLK, $\overline{ADTRG}$, RXD0, RXD1, RXD2, RXD3, CLK0, $\overline{CLK1}$, CLK2, CLK3, $\overline{CTS2}$, SSI, SCL, SDA, SSO, SSCK, $\overline{SCS}$			0.1	1.2	—	V
		$\overline{RESET}$			0.1	1.2	—	V
I_{IH}	Input "H" current		V_I = 5 V, V_{CC} = 5.0 V		—	—	5.0	µA
I_{IL}	Input "L" current		V_I = 0 V, V_{CC} = 5.0 V		—	—	–5.0	µA
R_{PULLUP}	Pull-up resistance		V_I = 0 V, V_{CC} = 5.0 V		25	50	100	kΩ
R_{fXIN}	Feedback resistance	XIN			—	0.3	—	MΩ
V_{RAM}	RAM hold voltage		During stop mode		1.8	—	—	V

Note:
1. 4.2 V ≤ V_{CC} ≤ 5.5 V, T_{opr} = –20 to 85 °C (N version)/-40 to 85 °C (D version), and f(XIN) = 20 MHz, unless otherwise specified.

Table 5.61 Electrical Characteristics (3) [2.7 V ≤ Vcc < 4.2 V]

Symbol	Parameter		Condition		Standard			Unit
					Min.	Typ.	Max.	
V_{OH}	Output “H” voltage	Other than XOUT	Drive capacity High	I_{OH} = –5 mA	V_{CC} – 0.5	—	V_{CC}	V
			Drive capacity Low	I_{OH} = –1 mA	V_{CC} – 0.5	—	V_{CC}	V
		XOUT		I_{OH} = –200 μA	1.0	—	V_{CC}	V
V_{OL}	Output “L” voltage	Other than XOUT	Drive capacity High	I_{OL} = 5 mA	—	—	0.5	V
			Drive capacity Low	I_{OL} = 1 mA	—	—	0.5	V
		XOUT		I_{OL} = 200 μA	—	—	0.5	V
V_{T+}-V_{T-}	Hysteresis	$\overline{INT0}$, $\overline{INT1}$, $\overline{INT2}$, $\overline{INT3}$, $\overline{INT4}$, $\overline{KI0}$, $\overline{KI1}$, $\overline{KI2}$, $\overline{KI3}$, TRAIO, TRCIOA, TRCIOB, TRCIOC, TRCIOD, TRFI, USB_OVRCURA, USB_VBUS, USB_ID, USB_OVRCURB, $\overline{TRCTRG}$, TRCCLK, $\overline{ADTRG}$, RXD0, RXD1, RXD2, RXD3, CLK0, $\overline{CLK1}$, CLK2, CLK3, $\overline{CTS2}$, SSI, SCL, $\overline{SDA}$, $\overline{SSO}$, SSCK, $\overline{SCS}$	V_{CC} = 3.0 V		0.1	0.4	—	V
		$\overline{RESET}$	V_{CC} = 3.0 V		0.1	0.5	—	V
I_{IH}	Input “H” current		V_I = 3 V, V_{CC} = 3.0 V		—	—	4.0	μA
I_{IL}	Input “L” current		V_I = 0 V, V_{CC} = 3.0 V		—	—	–4.0	μA
R_{PULLUP}	Pull-up resistance		V_I = 0 V, V_{CC} = 3.0 V		42	84	168	kΩ
R_{fXIN}	Feedback resistance	XIN			—	0.3	—	MΩ
V_{RAM}	RAM hold voltage		During stop mode		1.8	—	—	V

Note:
1. 2.7 V ≤ V_{CC} < 4.2 V, T_{opr} = –20 to 85 °C (N version)/-40 to 85 °C (D version), and f(XIN) = 10 MHz, unless otherwise specified.
2. 3.0 V ≤ VCC < 3.6 V for the USB associated pins.

Table 5.68 Electrical Characteristics (5) [1.8 V ≤ Vcc < 2.7 V]

Symbol	Parameter		Condition		Standard			Unit
					Min.	Typ.	Max.	
V_{OH}	Output “H” voltage	Other than XOUT	Drive capacity High	I_{OH} = –2 mA	V_{CC} – 0.5	—	V_{CC}	V
			Drive capacity Low	I_{OH} = –1 mA	V_{CC} – 0.5	—	V_{CC}	V
		XOUT		I_{OH} = –200 μA	1.0	—	V_{CC}	V
V_{OL}	Output “L” voltage	Other than XOUT	Drive capacity High	I_{OL} = 2 mA	—	—	0.5	V
			Drive capacity Low	I_{OL} = 1 mA	—	—	0.5	V
		XOUT		I_{OL} = 200 μA	—	—	0.5	V
V_{T+}-V_{T-}	Hysteresis	$\overline{INT0}$, $\overline{INT1}$, $\overline{INT2}$, $\overline{INT3}$, $\overline{INT4}$, $\overline{KI0}$, $\overline{KI1}$, $\overline{KI2}$, $\overline{KI3}$, TRAIO, TRCIOA, TRCIOB, TRCIOC, TRCIOD, TRFI, $\overline{TRCTRG}$, TRCCLK, $\overline{ADTRG}$, RXD0, RXD1, RXD2, RXD3, CLK0, $\overline{CLK1}$, CLK2, CLK3, $\overline{CTS2}$, SSI, SCL, SDA, $\overline{SSO}$, $\overline{SSCK}$, $\overline{SCS}$			0.05	0.20	—	V
		$\overline{RESET}$			0.05	0.20	—	V
I_{IH}	Input “H” current		V_I = 2.2 V, V_{CC} = 2.2 V		—	—	4.0	μA
I_{IL}	Input “L” current		V_I = 0 V, V_{CC} = 2.2 V		—	—	–4.0	μA
R_{PULLUP}	Pull-up resistance		V_I = 0 V, V_{CC} = 2.2 V		70	140	300	kΩ
R_{fXIN}	Feedback resistance	XIN			—	0.3	—	MΩ
V_{RAM}	RAM hold voltage		During stop mode		1.8	—	—	V

Note:
1. 1.8 V ≤ V_{CC} < 2.7 V, T_{opr} = –20 to 85 °C (N version)/-40 to 85 °C (D version), and f(XIN) = 5 MHz, unless otherwise specified.